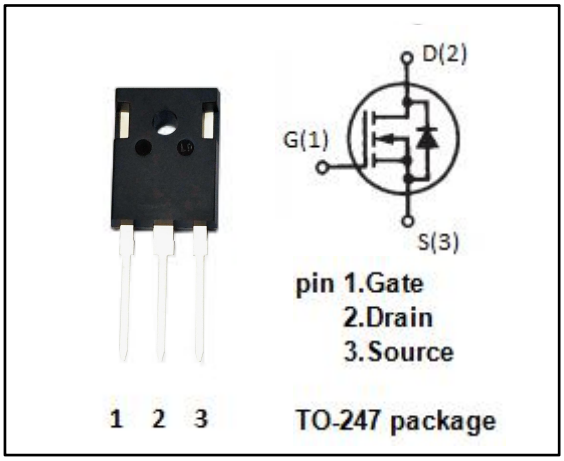
Isc N-Channel MOSFET Transistor IXTX110N20L2

- **FEATURES**
- With TO-3PL package
- Low input capacitance and gate charge
- High speed switching
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

- **APPLICATIONS**
- Switching applications
- Load switch
- Power management

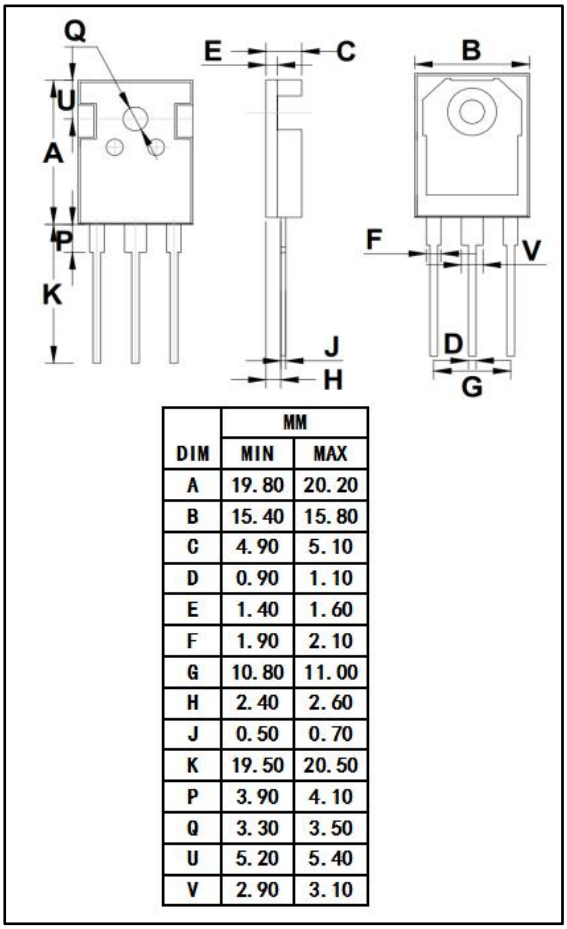


- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V_{GSS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous	110	A
I_{DM}	Drain Current-Single Pulsed	275	A
P_D	Total Dissipation @T_C=25℃	960	W
Tj	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.13	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62.5	℃/W



DIM	MM MIN	MM MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 1mA	200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=3mA	2.0		4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=55A			24	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0V			±0.2	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=200V; V_{GS}= 0V;Tc=25℃ Tc=125℃			50 2500	μA
V_{SDF}	Diode forward voltage	I_{SD}=55A, V_{GS} = 0V			1.35	V